



YOUSHANG SEMICONDUCTOR

设计研发新型功率器件

各类小信号开关

中低压及高压大电流等场效应管

0755-83047638
ysbdt@szyoushang.cn
www.szyoushang.cn



企业微信二维码



企业QQ二维码

Features

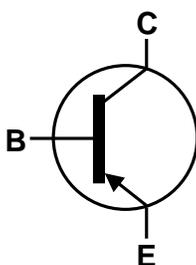
- $BV_{CEO} > -60V$
- $I_C = -600mA$ Collector Current
- Epitaxial Planar Die Construction
- Ultra-Small Surface Mount Package
- Complementary NPN Type: NK-MMST2222A

Mechanical Data

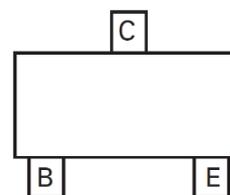
- Case: SOT323
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish – Matte Tin Plated Leads. Solderable per MIL-STD-202, Method 208 
- Weight: 0.006 grams (Approximate)



Top View



Device Symbol



Pin-Out Top View

Absolute Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CB0}	-60	V
Collector-Emitter Voltage	V _{CEO}	-60	V
Emitter-Base Voltage	V _{EBO}	-5	V
Collector Current	I _C	-600	mA

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 6)	P _D	200	mW
Thermal Resistance, Junction to Ambient (Note 6)	R _{θJA}	625	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

ESD Ratings (Note 7)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	C

Notes: 6. For a device mounted with the collector lead on minimum recommended pad layout 1oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in a steady-state.
 7. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

Thermal Characteristics and Derating Information

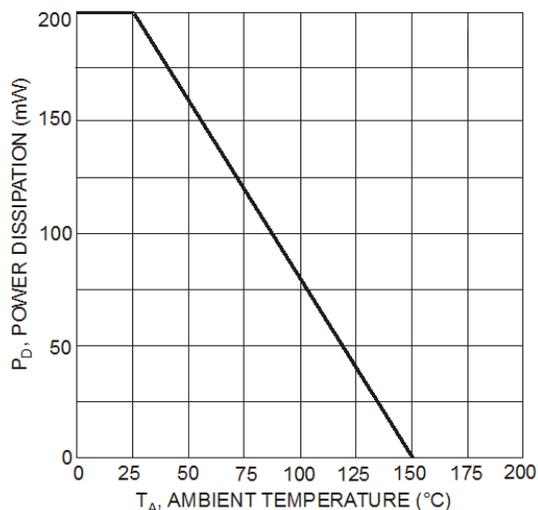


Fig. 1 Max Power Dissipation vs. Ambient Temperature

Electrical Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Min	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)					
Collector-Base Breakdown Voltage	BV_{CBO}	-60	—	V	$I_C = -10\mu\text{A}, I_E = 0$
Collector-Emitter Breakdown Voltage	BV_{CEO}	-60	—	V	$I_C = -10\text{mA}, I_B = 0$
Emitter-Base Breakdown Voltage	BV_{EBO}	-5	—	V	$I_E = -10\mu\text{A}, I_C = 0$
Collector Base Cutoff Current	I_{CBO}	—	-10	nA μA	$V_{CB} = -50\text{V}, I_E = 0$ $V_{CB} = -50\text{V}, I_E = 0, T_A = +125^\circ\text{C}$
Collector Cutoff Current	I_{CEX}	—	-50	nA	$V_{CE} = -30\text{V}, V_{EB(OFF)} = -0.5\text{V}$
Base Cutoff Current	I_{BL}	—	-50	nA	$V_{CE} = -30\text{V}, V_{EB(OFF)} = -0.5\text{V}$
ON CHARACTERISTICS (Note 8)					
DC Current Gain	h_{FE}	75 100 100 100 50	— — — 300 —	—	$I_C = -100\mu\text{A}, V_{CE} = -10\text{V}$ $I_C = -1\text{mA}, V_{CE} = -10\text{V}$ $I_C = -10\text{mA}, V_{CE} = -10\text{V}$ $I_C = -150\text{mA}, V_{CE} = -10\text{V}$ $I_C = -500\text{mA}, V_{CE} = -10\text{V}$
Collector-Emitter Saturation Voltage	$V_{CE(SAT)}$	—	-0.4 -1.6	V	$I_C = -150\text{mA}, I_B = -15\text{mA}$ $I_C = -500\text{mA}, I_B = -50\text{mA}$
Base-Emitter Saturation Voltage	$V_{BE(SAT)}$	—	1.3 2.6	V	$I_C = -150\text{mA}, I_B = -15\text{mA}$ $I_C = -500\text{mA}, I_B = -50\text{mA}$
SMALL SIGNAL CHARACTERISTICS					
Output Capacitance	C_{OBO}	—	8	pF	$V_{CB} = -10\text{V}, f = 1.0\text{MHz}, I_E = 0$
Input Capacitance	C_{IBO}	—	30	pF	$V_{EB} = -2\text{V}, f = 1.0\text{MHz}, I_C = 0$
Current Gain-Bandwidth Product	f_T	200	—	MHz	$V_{CE} = -20\text{V}, I_C = -50\text{mA}, f = 100\text{MHz}$
SWITCHING CHARACTERISTICS					
Turn-On Time	t_{ON}	—	45	ns	$V_{CC} = -30\text{V}, I_C = -150\text{mA}, I_{B1} = -15\text{mA}$
Delay Time	t_D	—	10	ns	
Rise Time	t_R	—	40	ns	
Turn-Off Time	t_{OFF}	—	100	ns	$V_{CC} = -6\text{V}, I_C = -150\text{mA}, I_{B1} = I_{B2} = -15\text{mA}$
Storage Time	t_S	—	80	ns	
Fall Time	t_F	—	30	ns	

Note: 8. Measured under pulsed conditions. Pulse width $\leq 300\mu\text{s}$. Duty cycle $\leq 2\%$.

Typical Electrical Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

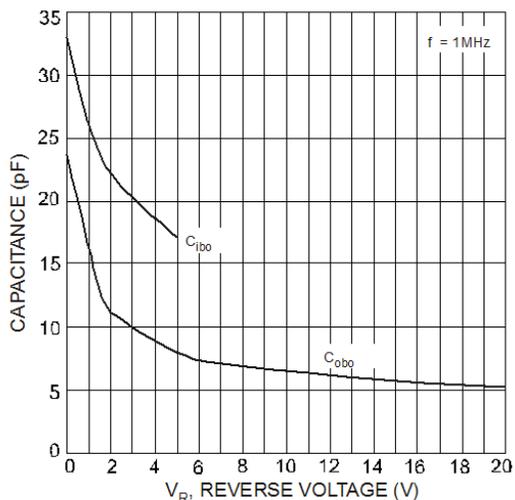


Fig. 2 Typical Capacitance Characteristics

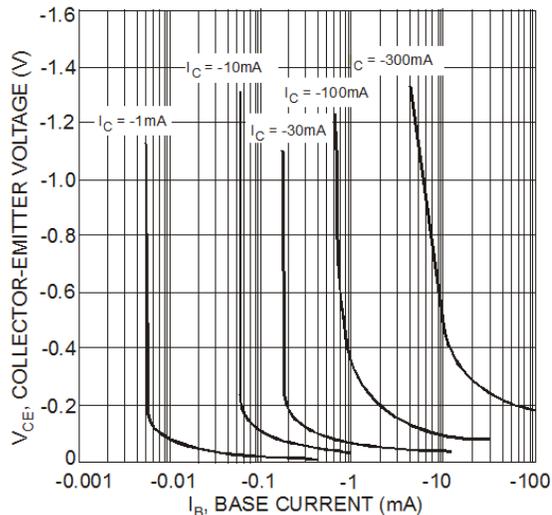


Fig. 3 Typical Collector Saturation Region

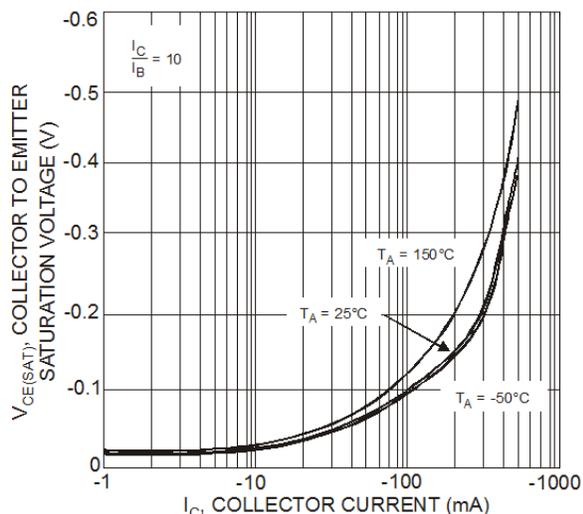


Fig. 4 Collector-Emitter Saturation Voltage vs. Collector Current

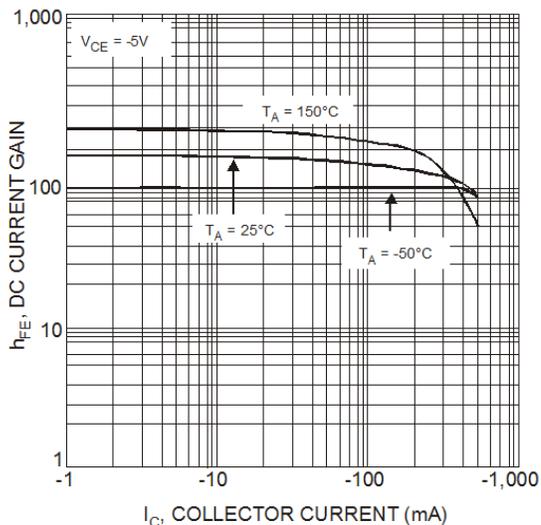


Fig. 5 DC Current Gain vs. Collector Current

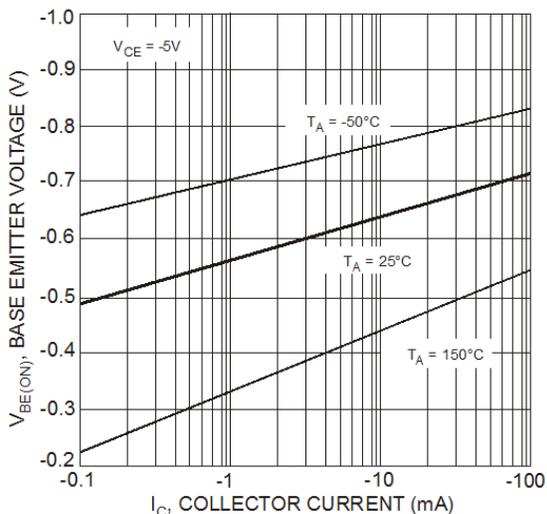


Fig. 6 Base-Emitter Voltage vs. Collector Current

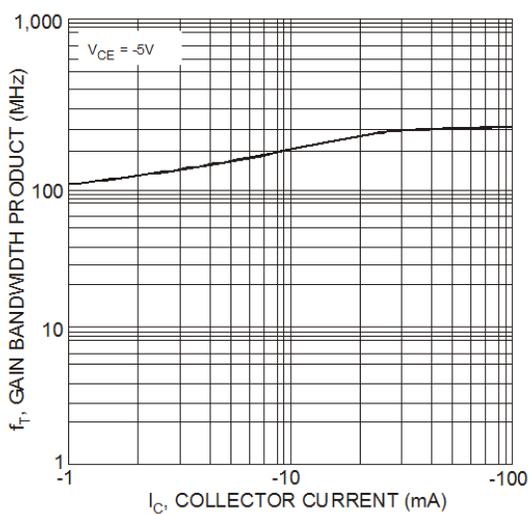
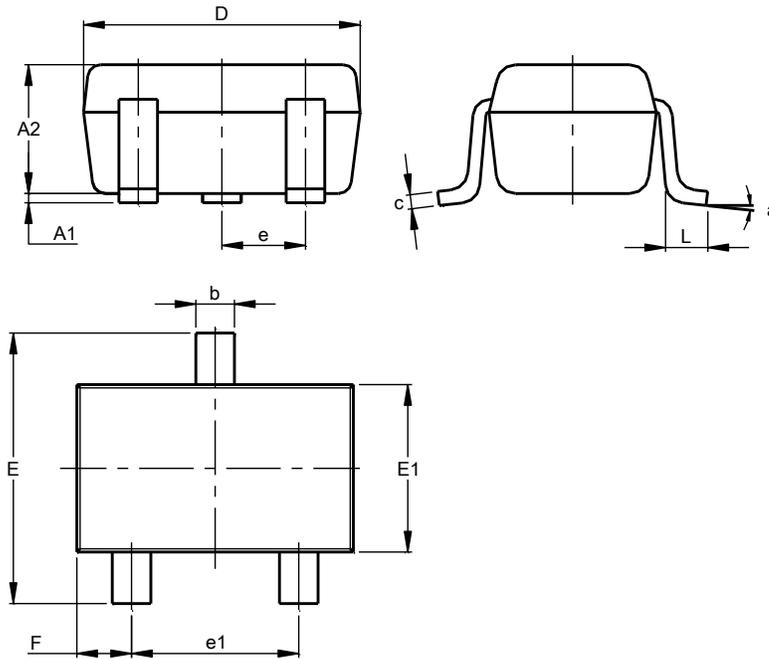


Fig. 7 Gain Bandwidth Product vs. Collector Current

Package Outline Dimensions

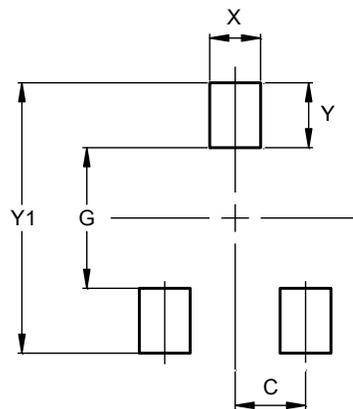
SOT323



SOT323			
Dim	Min	Max	Typ
A1	0.00	0.10	0.05
A2	0.90	1.00	0.95
b	0.25	0.40	0.30
c	0.10	0.18	0.11
D	1.80	2.20	2.15
E	2.00	2.20	2.10
E1	1.15	1.35	1.30
e	0.650 BSC		
e1	1.20	1.40	1.30
F	0.375	0.475	0.425
L	0.25	0.40	0.30
a	0°	8°	-
All Dimensions in mm			

Suggested Pad Layout

SOT323



Dimensions	Value (in mm)
C	0.650
G	1.300
X	0.470
Y	0.600
Y1	2.500